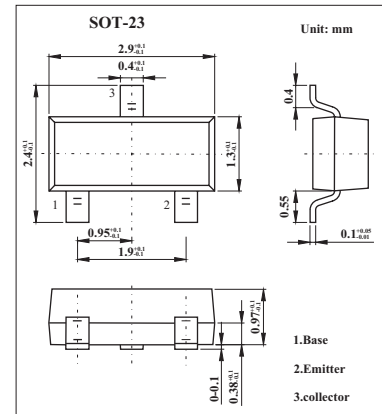


Silicon NPN Epitaxial

2SC3265

■ Features

- High DC current gain: $h_{FE}(1) = 100\sim 320$.
- Low saturation voltage: $V_{CE(sat)} = 0.4\text{ V (max)}$
($I_C = 500\text{ mA}$, $I_B = 20\text{ mA}$).

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	800	mA
Base current	I_B	160	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 30\text{ V}$, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 50\text{ V}$, $I_C = 0$			0.1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}$, $I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.1\text{ mA}$, $I_C = 0$	5			V
DC current gain	h_{FE}	$V_{CE} = 1\text{ V}$, $I_C = 100\text{ mA}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{ mA}$, $I_B = 20\text{ mA}$			0.4	V
Base-emitter voltage	V_{BE}	$V_{CE} = 1\text{ V}$, $I_C = 10\text{ mA}$	0.5		0.8	V
Transition frequency	f_T	$V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$		13		pF

■ h_{FE} Classification

Marking	EO	EY
h_{FE}	100~200	160~320